# MC14106B

# **Hex Schmitt Trigger**

The MC14106B hex Schmitt Trigger is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These devices find primary use where low power dissipation and/or high noise immunity is desired. The MC14106B may be used in place of the MC14069UB hex inverter for enhanced noise immunity or to "square up" slowly changing waveforms.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in}$  or  $V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

#### **Features**

- Increased Hysteresis Voltage Over the MC14584B
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range
- Pin-for-Pin Replacement for CD40106B and MM74C14
- Can Be Used to Replace the MC14584B or MC14069UB
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### **MAXIMUM RATINGS** (Voltages Referenced to V<sub>SS</sub>)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C



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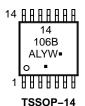




SOIC-14 NB D SUFFIX CASE 751A TSSOP-14 DT SUFFIX CASE 948G

#### MARKING DIAGRAMS





= Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

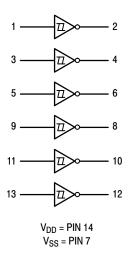


Figure 1. Logic Diagram

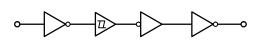


Figure 2. Equivalent Circuit Schematic (1/6 of Circuit Shown)

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14106BDG	SOIC-14 NB (Pb-Free)	55 Units / Rail
NLV14106BDG*	SOIC-14 NB (Pb-Free)	55 Units / Rail
MC14106BDR2G	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
NLV14106BDR2G*	SOIC-14 NB (Pb-Free)	2500 / Tape & Reel
MC14106BDTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLV14106BDTR2G*	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure BRD8011/D

Specifications Brochure, BRD8011/D.
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

#### MC14106B

### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-5	5°C		25°C		12	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub>	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V <sub>in</sub> = 0	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15		4.95 9.95 14.95	- - -	Vdc
Hysteresis Voltage		V <sub>H</sub> <sup>(5)</sup>	5.0 10 15	0.3 1.2 1.6	2.0 3.4 5.0	0.3 1.2 1.6	1.1 1.7 2.1	2.0 3.4 5.0	0.3 1.2 1.6	2.0 3.4 5.0	Vdc
Threshold Voltage Positive–Going		V <sub>T+</sub>	5.0 10 15	2.2 4.6 6.8	3.6 7.1 10.8	2.2 4.6 6.8	2.9 5.9 8.8	3.6 7.1 10.8	2.2 4.6 6.8	3.6 7.1 10.8	Vdc
Negative-Going		V <sub>T-</sub>	5.0 10 15	0.9 2.5 4.0	2.8 5.2 7.4	0.9 2.5 4.0	1.9 3.9 5.8	2.8 5.2 7.4	0.9 2.5 4.0	2.8 5.2 7.4	Vdc
Output Drive Current $(V_{OH} = 2.5 \text{ Vdc})$ $(V_{OH} = 4.6 \text{ Vdc})$ $(V_{OH} = 9.5 \text{ Vdc})$ $(V_{OH} = 13.5 \text{ Vdc})$	Source	I <sub>OH</sub>	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4	- - - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8		0.36 0.9 2.4	- - -	mAdc
Input Current		l <sub>in</sub>	15	_	±0.1	_	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	-	-	-	_	5.0	7.5	_	-	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C <sub>L</sub> = 50 pF on all output buffers switching)	nt,	I <sub>T</sub>	5.0 10 15			$I_T = (3)$	1.8 μΑ/kHz) f 3.6 μΑ/kHz) f 5.4 μΑ/kHz) f	+ I <sub>DD</sub>			μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>2.</sup> Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

<sup>3.</sup> The formulas given are for the typical characteristics only at 25  $^{\circ}\text{C}.$ 

To calculate total supply current at loads other than 50 pF:
 I<sub>T</sub>(C<sub>L</sub>) = I<sub>T</sub>(50 pF) + (C<sub>L</sub> – 50) Vfk where I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> – V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.001.

<sup>5.</sup>  $V_H = V_{T+} - V_{T-}$  (But maximum variation of  $V_H$  is specified as less that  $V_{T+max} - V_{T-min}$ ).

# **SWITCHING CHARACTERISTICS** ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time	t <sub>TLH</sub>	5.0	_	100	200	ns
		10	_	50	100	
		15	_	40	80	
Output Fall Time	t <sub>THL</sub>	5.0	_	100	200	ns
		10	_	50	100	
		15	_	40	80	
Propagation Delay Time	t <sub>PLH</sub> , t <sub>PHL</sub>	5.0	_	125	250	ns
		10	_	50	100	
		15	_	40	80	

<sup>6.</sup> Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

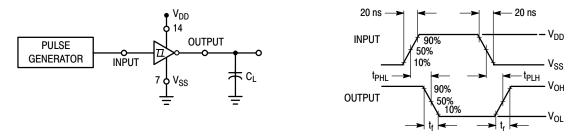
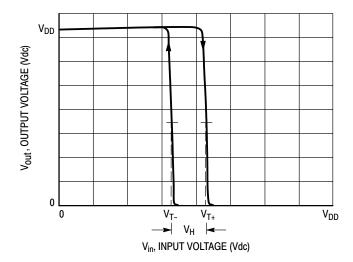


Figure 1. Switching Time Test Circuit and Waveforms



**Figure 2. Typical Transfer Characteristics** 

# **APPLICATIONS**

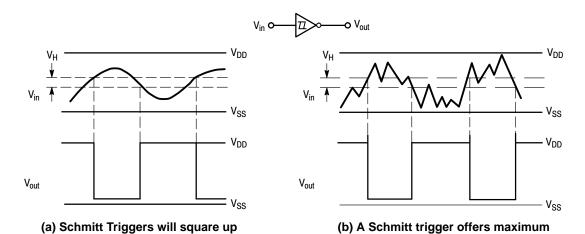


Figure 3.

noise immunity in gate applications.

inputs with slow rise and fall times.

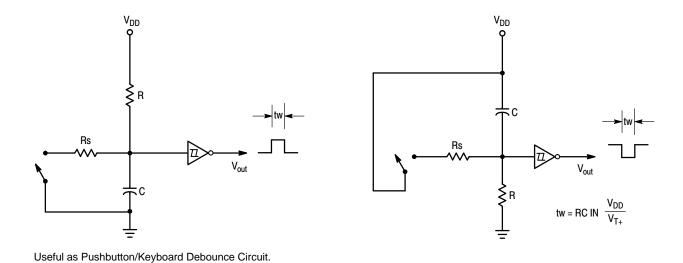


Figure 4. Monostable Multivibrator

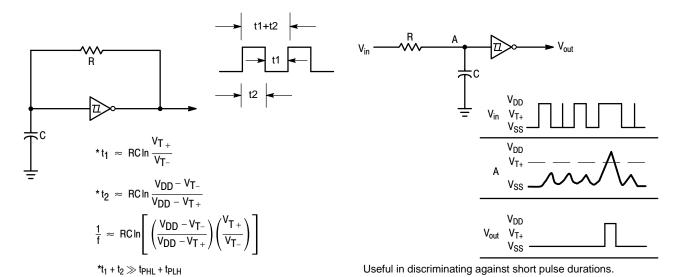
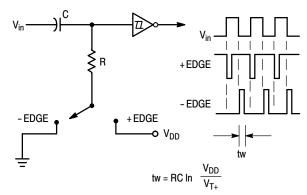


Figure 5. Astable Multivibrator

Figure 6. Integrator



Useful as an edge detector circuit.

Figure 7. Differentiator

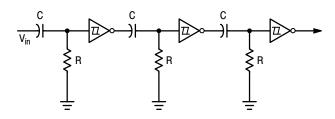
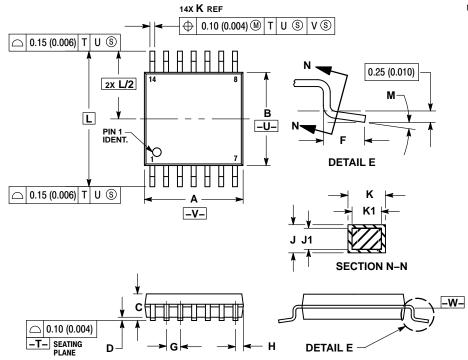


Figure 8. Positive Edge Time Delay Circuit

### MC14106B

#### PACKAGE DIMENSIONS

#### TSSOP-14 CASE 948G **ISSUE B**



- JIES:

  1. DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD
  FLASH, PROTRUSIONS OR GATE BURRS.
  MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL
- NOT EXCEED 0.25 (0.010) PER SIDE.

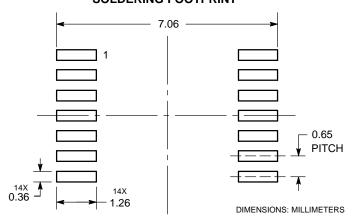
  5. DIMENSION K DOES NOT INCLUDE
  DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08
  (0.003) TOTAL IN EXCESS OF THE K
  DIMENSION AT MAXIMUM MATERIAL
  CONDITION. CONDITION.
- CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
Κ	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
Г	6.40 BSC		0.252	BSC
M	0°	8 °	0°	8 °

# **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

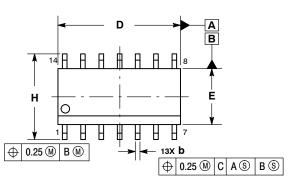


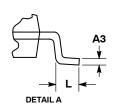


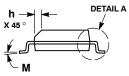
△ 0.10

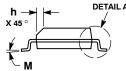
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**DATE 03 FEB 2016** 





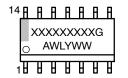




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE
  MOLD PROTRUSIONS.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# **SOLDERING FOOTPRINT\***

1	6.50 —		4X .18
			1.27
		-	PITCH
14X A			<u> </u>
0.58			

**DIMENSIONS: MILLIMETERS** \*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **STYLES ON PAGE 2**

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## SOIC-14 CASE 751A-03 ISSUE L

# DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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